

BCW66GLT1G, SBCW66GLT1G

General Purpose Transistor

NPN Silicon

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	45	Vdc
Collector–Base Voltage	V_{CBO}	75	Vdc
Emitter–Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	800	mAdc
Collector Current – Pulsed	I_C	1200	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

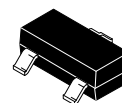
1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

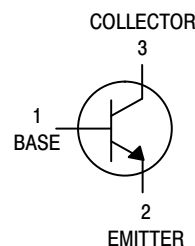


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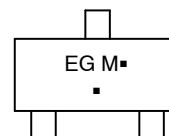
<http://onsemi.com>



SOT-23
(TO-236)
CASE 318-08
STYLE 6



MARKING DIAGRAM



EG = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(*Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SBCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
BCW66GLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	45	–	–	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $V_{EB} = 0$)	$V_{(BR)CES}$	75	–	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector Cutoff Current ($V_{CE} = 45\text{ Vdc}$, $I_E = 0$) ($V_{CE} = 45\text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CES}	– –	– –	20 20	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	50 110 160 60	– – – –	– – 400 –	–
Collector–Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	– –	– –	0.7 0.3	Vdc
Base–Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{BE(sat)}$	–	–	2.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 20\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	–	12	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	–	80	pF
Noise Figure ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 0.2\text{ mAdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	–	–	10	dB

SWITCHING CHARACTERISTICS

Turn–On Time ($I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_{on}	–	–	100	ns
Turn–Off Time ($I_C = 150\text{ mAdc}$, $R_L = 150\text{ }\Omega$)	t_{off}	–	–	400	ns

TYPICAL CHARACTERISTICS

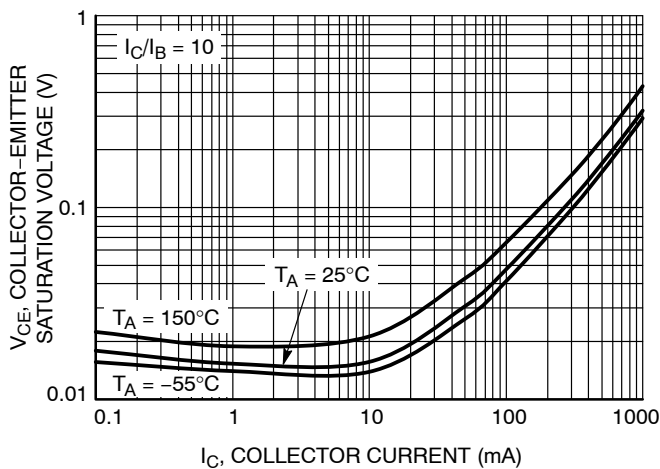


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

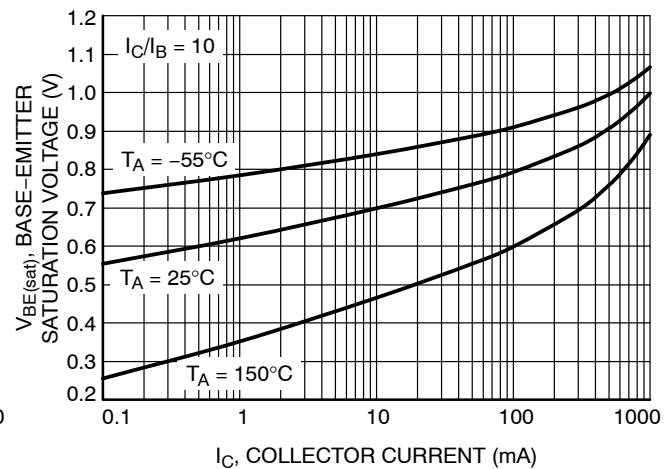


Figure 2. Base Emitter Saturation Voltage vs. Collector Current

BCW66GLT1G, SBCW66GLT1G

TYPICAL CHARACTERISTICS

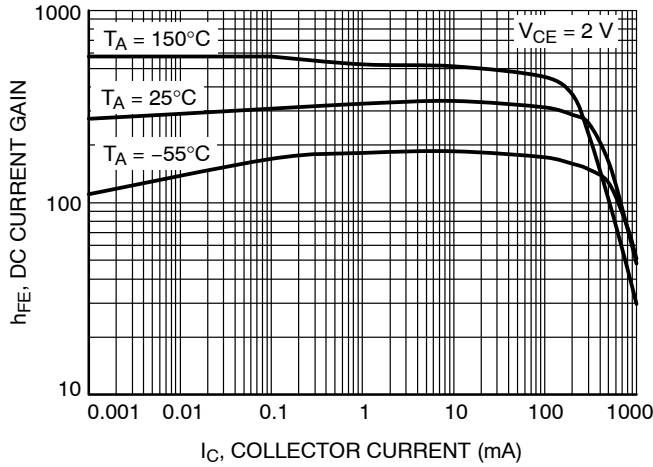


Figure 3. DC Current Gain vs. Collector Current

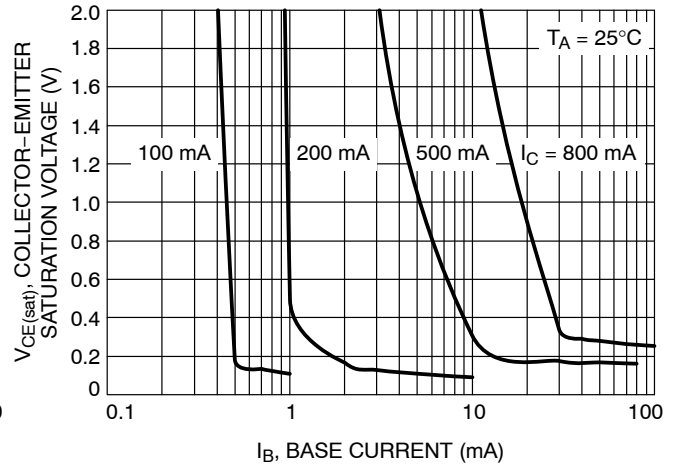


Figure 4. Saturation Region

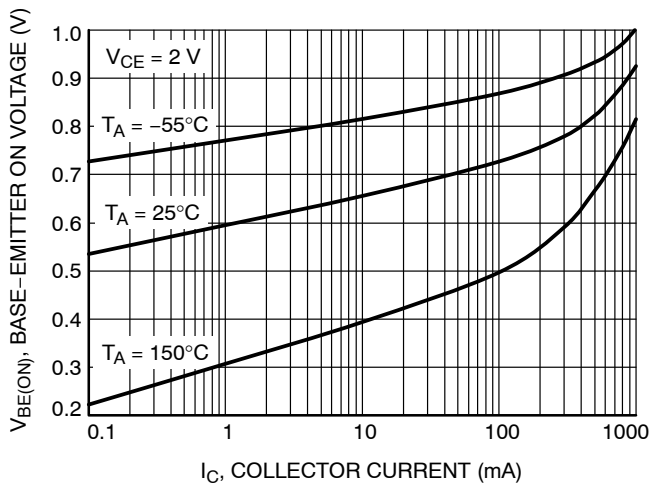


Figure 5. Base-Emitter Turn-On Voltage vs. Collector Current

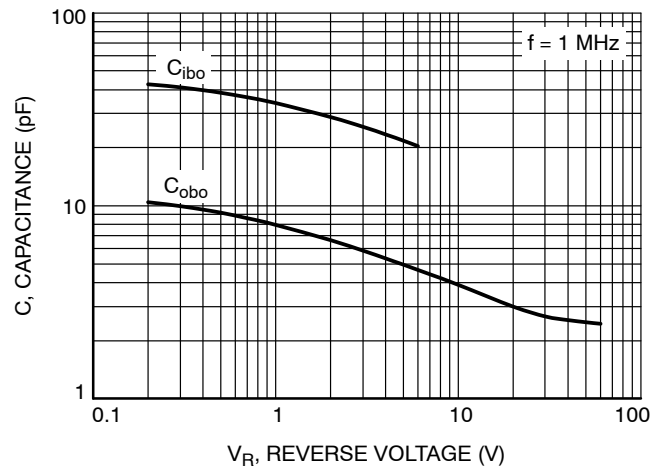


Figure 6. Capacitance

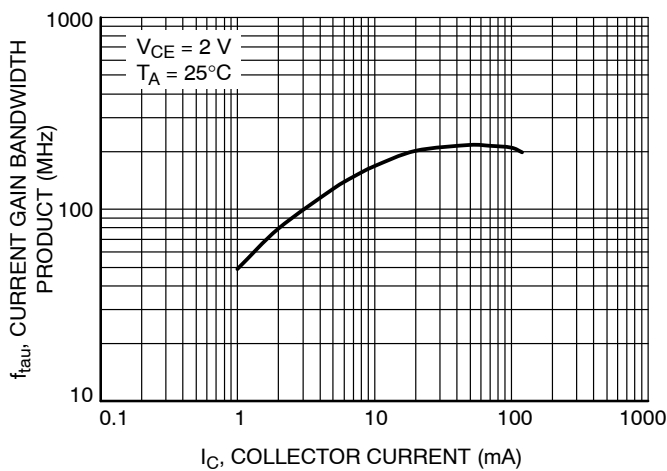


Figure 7. Current Gain Bandwidth Product vs. Collector Current

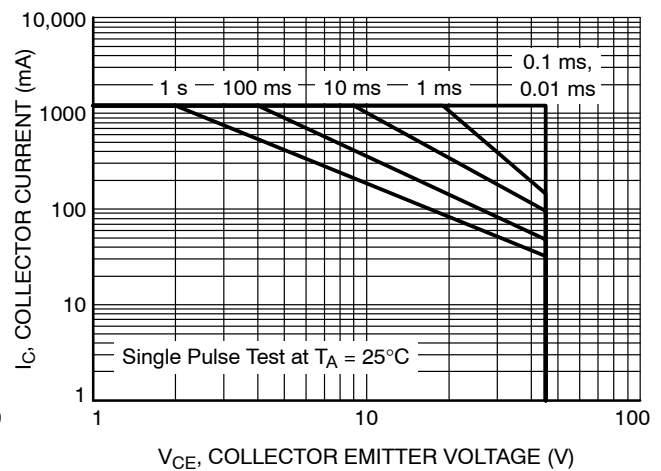
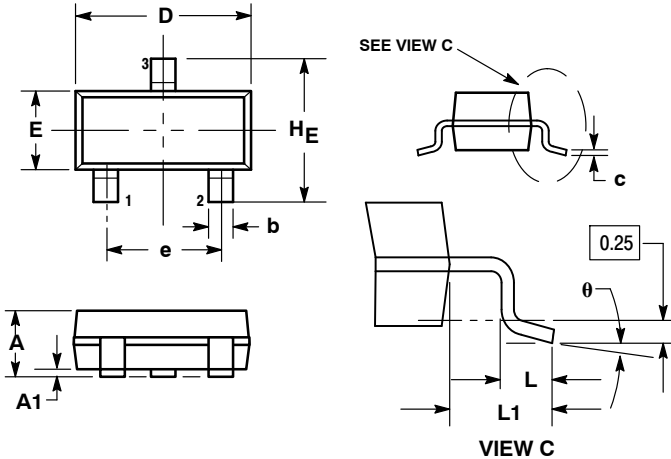


Figure 8. Safe Operating Area

BCW66GLT1G, SBCW66GLT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

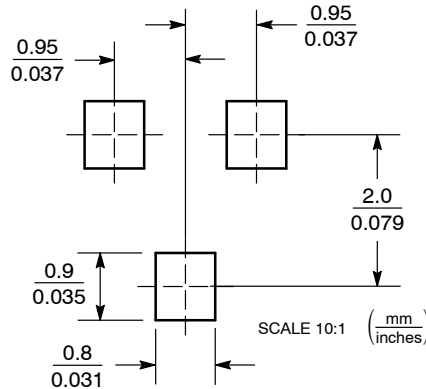
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104
theta	0°	---	10°	0°	---	10°

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT



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